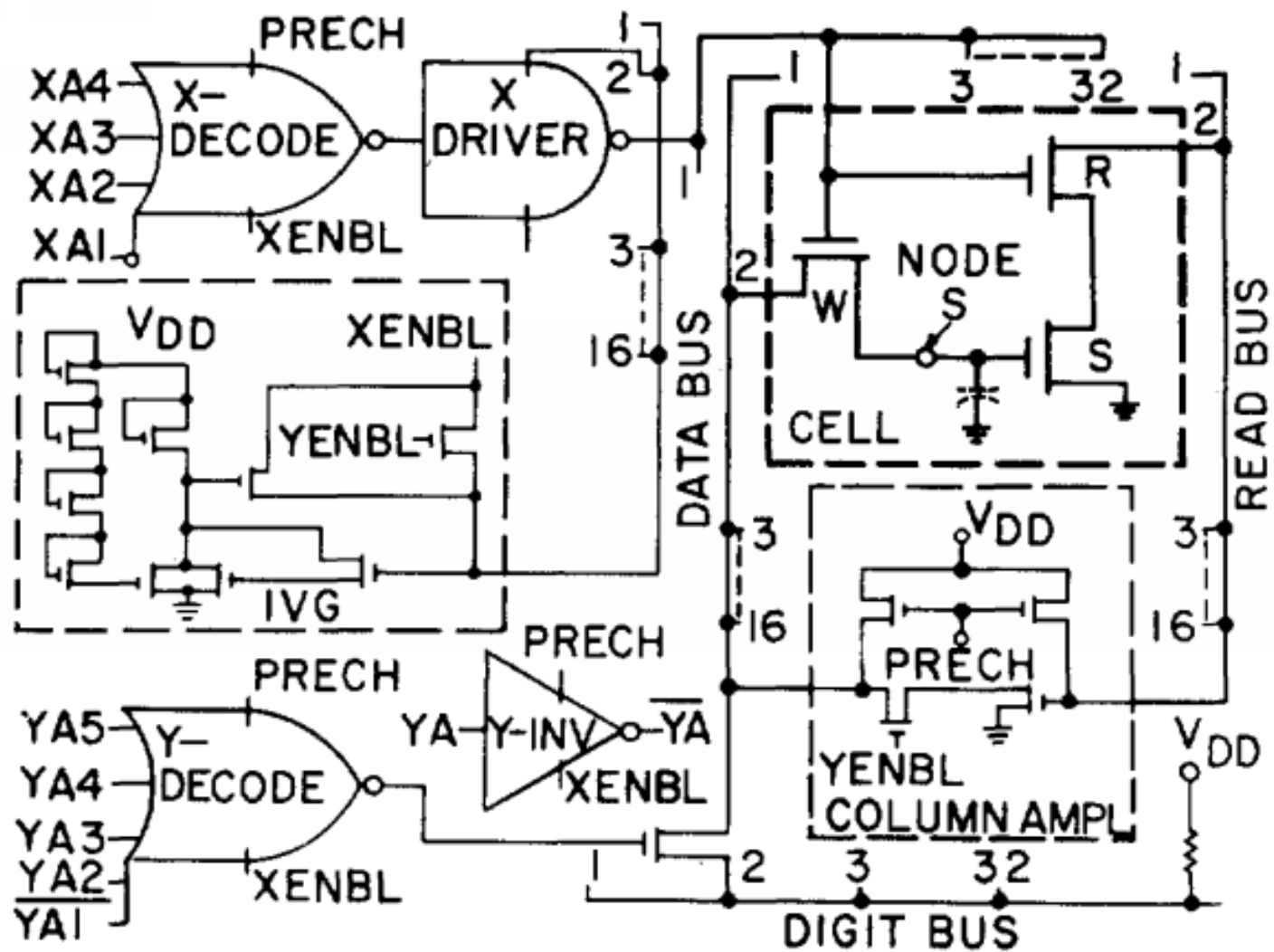


# FIRST 1K MOS DRAM

ISSCC 1970



## A Three-Transistor-Cell, 1024-Bit, 500NS MOS RAM

THE 1970 PAPER by Regitz (Honeywell) and Karp (Intel) was the ground breaking work for the future development of DRAMs. Using a three transistor cell, 1024 bit memory density was achieved. The read speed for this device was 345ns and the power consumption was 50 $\mu$ W per bit. The “16 pin package” used in this work became the DRAM package of choice for many years to come.